



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Hisato OYAMATSU

Serial No.: 09/917,775

Filed: July 31, 2001

For: SEMICONDUCTOR DEVICE

Atty. Docket No.: 002372.00027

Group Art Unit: 2811

Examiner: Hu, S.

Confirmation No.: 1487

2811
#11/B
11/22/02
HAYES

RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Notice of Non-Compliant Amendment mailed October 30, 2002, Applicant submits herewith a "Replacement Amendment" which fully replaces the Amendment submitted to the U.S. Patent and Trademark Office on October 22, 2002 in response to the Office Action mailed May 22, 2002. The Replacement Amendment is in full compliance with the rules under 37 C.F.R. §§ 1.121(b)(ii) and 1.121(b)(iii).

It is believed that no fee is required for this submission. If any fees are required or if an overpayment is made, the Commissioner is authorized to debit or credit our Deposit Account No. 19-0733, accordingly.

Respectfully submitted,

BANNER & WITCOFF, LTD.

Dated: 11/12/02

By:

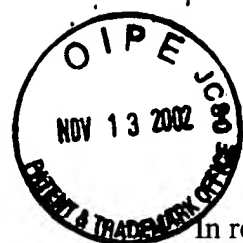
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REPLACEMENT AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

PETITION FOR EXTENSION OF TIME

This paper is responsive to the Office Action mailed May 22, 2002. Applicant requests a two (2) month extension of time until October 22, 2002. The Commissioner is authorized to charge our Deposit Account No. 19-0733 in the amount of \$400.00 (a Fee Transmittal is attached). If additional fees are required or if an overpayment is made, the Commissioner is authorized to charge or credit our Deposit Account No. 19-0733, accordingly.

In response to the Office Action mailed May 22, 2002, please amend the instant application as follows:

IN THE SPECIFICATION:

Please replace the paragraph on page 2, lines 4-7, with the following rewritten paragraph:

B'
In case of Fig. 9A, an n^+ diffusion layer 15, which is a device region, is formed on the surface part of the p-well 13, but no device region exists in the opposite position in the n-well side. This is called an open space.

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